PATENT S/N 10/765,301

## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Matthew C. Landau Applicant: Terrence C. Leslie Examiner: Group Art Unit: 2815 Serial No.: 10/765,301

January 27, 2004 303.860US1 Filed: Docket: SELECTIVE EPITAXY VERTICAL INTEGRATED CIRCUIT COMPONENTS Title:

AND METHODS

## SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

MS Amendment Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

In compliance with the duty imposed by 37 C.F.R. § 1.56, and in accordance with 37 C.F.R. 88 1.97 et. seg., the enclosed materials are brought to the attention of the Examiner for consideration in connection with the above-identified patent application. Applicant respectfully requests that this Supplemental Information Disclosure Statement be entered and the documents listed on the attached Form 1449 be considered by the Examiner and made of record. Pursuant to the provisions of MPEP 609, Applicant requests that a copy of the 1449 form, initialed as being considered by the Examiner, be returned to the Applicant with the next official communication.

Pursuant to 37 C.F.R. §1.97(c)(2), Applicants hereby authorize the Commissoner to charge the fee of \$180.00 as set forth in 37 C.F.R. §1.17(p), to Deposit Account No. 19-0743. Please charge any additional fees or credit any overpayment to Deposit Account No. 19-0743. Filing Date: January 27, 2004 Title: SELECTIVE EPITAXY VERTICAL INTEGRATED CIRCUIT COMPONENTS AND METHODS

The Examiner is invited to contact the Applicant's Representative at the below-listed telephone number if there are any questions regarding this communication.

Pursuant to 37 C.F.R. 1,98(a)(2), Applicant believes that copies of cited U.S. Patents and Published Applications are no longer required to be provided to the Office. Notification of this change was provided in the United States Patent and Trademark Office OG Notices dated October 12, 2004. Thus, Applicant has not included copies of any US Patents or Published Applications cited with this submission. Should the Office require copies to be provided. Applicant respectfully requests that notice of such requirement be directed to Applicant's belowsigned representative. Applicant acknowledges the requirement to submit copies of foreign patent documents and non-patent literature in accordance with 37 C.F.R. 1.98(a)(2).

Respectfully submitted,

TERRENCE C. LESLIE

By his Representatives,

SCHWEGMAN, LUNDBERG, WOESSNER & KLUTH, P.A. P.O. Box 2938 Minneapolis, MN 55402 (612) 349-9587

Timothy B Clis Reg. No. 40,957

ondence is being filed using the USSER/selectr CERTIFICATE UNDER 37 CFR 1.8: The undersigned hereby certifies that this corr ady West Sto Hey 2006 filing system EFS-Web, and is addressed to: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450, on this

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INFORMATION DISCLOSURE
STATEMENT BY APPLICANT
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Application Number	10/765,301	
Filing Date	January 27, 2004	
First Named Inventor	Leslie, Terrence	
Group Art Unit	2815	
Examiner Name	Landau, Matthew	

Sheet 1 of 1

US PATENT DOCUMENTS						
Examiner Initial *	USP Document Number	Publication Date	Name of Petentee or Applicant of cited Document	Filing Date If Appropriate		
	US-6.687.146	02/03/2004	Kurjanowicz, Włodek , et al.	01/31/2002		

Attorney Docket No: 303.860US1

FOREIGN PATENT DOCUMENTS								
mise or Applicant of cited T2								

	OTHE	R DOCUMENTS - NON PATENT LITERATURE DOCUMENTS	
Exeminer Initiale*	Cite No 1	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journel, earlel, sympoelum, catalog, etc.), date, page(s), volume-leave number(s), publisher, city endors country where published.	_
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		ISA, "IBM claims speediest silicon transistor", http://www.isa.org/Template.cfm/Section=Communities&template=/TaggedPage /Detail/Display.cfm&ContentID=20445, ISA - The Instrumentation, Systems and Automation Society,(November 4, 2002),2 pgs	
		LUCENT TECHNOLOGIES, "Revolutionary transistor design turns the silicon world on end", http://www.bell-labs.com/news/1999/november/15/1.html, Lucent Technologies, Bell Labs Innovations, (1999), 3 pps	
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EXAMINER

DATE CONSIDERED